

Junction Structure and Junction Method for Conductive Projection

Cross Reference To Related Applications

5 [0001]

The present document is based on Japanese Priority Document JP2003-077343, filed in the Japanese Patent Office on March 20, 2003, the entire contents of which being incorporated herein by reference.

10

Background of the Invention

1. Field of the Invention

[0002]

15 The present invention relates to a junction structure and a junction method of conductive projection used for making electrical and mechanical connection when mounting, for example, semiconductor parts on a wiring board, such as a mother board. More particularly, the present invention is related to a junction structure of conductive projection, which is
20 joined to a planarized surface having no steps by surrounding its root portion with a resin material in a ring form to have high junction strength, and to a junction method of the conductive projection.

25 2. Description of Related Art

[0003]

In recent years, as electronic apparatuses are being further miniaturized and sophisticated, there are increasing demands for semiconductor parts to be mounted that should be
30 more sophisticated and be even thinner, so that the semiconductor parts tend to have more and more pins. For

meeting the demands, when rearrangement of chip electrode portions on an interposer is conducted without changing the wiring rule, the number of layers in the interposer is increased, causing a problem of an increase in the thickness of a package.

- 5 Therefore, an interposer at a high wiring density which meets the demands of the increase of pins without sacrificing reduction of the thickness of the package is desired.

[0004]

- 10 The increase of pins causes a bare chip to be larger, thus increasing the size of a package having the bare chip mounted. In accordance with this tendency, higher junction reliability is required in the junction between the package and the mother board.

[0005]

- 15 In view of the above, for example, Patent document 1 has proposed a structure in which the root portion of the conductive projection joined onto an interposer is surrounded by a resin material to reinforce there.

[0006]

- 20 [Patent document 1]

Japanese Patent No. 2842361

Summary of the Invention

[0007]

- 25 When a periphery of the root portion of the conductive projection is reinforced by a resin material, it is important that the reinforcing resin material is supplied uniformly to the periphery of the root portion of each conductive projection. In Patent document 1, as shown in FIG. 12, there is a step
30 between the surface of an insulating layer 11 and a conductor portion 12. For this reason, when applying the reinforcing

resin material to the root portion of the conductive projection, the resin material is disadvantageously supplied along the steps, so that the amount of the resin material supplied is not uniform and a fillet 46 at a certain position cannot have
5 a satisfactory height, leading to a disadvantage in that the junction strength may be lowered.

[0008]

When the amount of the resin material supplied is increased for obtaining a desired fillet height or preventing
10 the fillet from having an ununiform height, shrinkage on curing of the increased resin material causes strain in the interposer, so that a problem in that the semiconductor package suffers warpage is likely to occur. This is remarkable especially in the thinner interposer.

15 [0009]

As a method for avoiding the warpage, there is a method in which the reinforcing resin material is supplied by a screen printing process only to the conductor portion to which the conductive projection is joined, but this method has a problem
20 in that printing is difficult when the pitches between the conductive projections are narrower.

[0010]

In view of the above, there are needs for providing a junction structure and a junction method for conductive
25 projection by which a required reinforcement strength may be obtained while suppressing the amount of a reinforcing resin material supplied to prevent the occurrence of warpage due to the shrinkage on curing of the resin material.

[0011]

30 For addressing the above needs, the junction structure for conductive projection of the present invention has a

characteristic feature such that the conductive projection is joined to the surface of the conductor portion which is formed at the same level as that of the surface of the insulating layer so that a root portion of the conductive projection is
5 surrounded by a resin material in a ring form.

[0012]

When the surface of the conductor portion is formed at the same level as that of the surface of the insulating layer and there are no steps on the surface, the resin material is
10 prevented from flowing into a gap. Further, even when the amount of the resin material supplied is small, a larger amount of the resin material may be allowed to wet and rise the root portion of the conductive projection, thereby enabling reinforcement by the resin material having a uniform height
15 required for securing a satisfactory strength of the junction portion.

[0013]

The reinforcing resin material does not cover the entire portion of the conductive projection but surrounds the root
20 portion of the conductive projection so as to be in a ring form. Therefore, if failure or defect is detected after the junction is made, such conductive projection may be repaired. The fused resin material is likely to wet the root portion of the conductive projection so as to be in a fillet form.
25 The resin material in a fillet form is a resin material having a form such that its thickness gradually decreases in a direction from the root portion to the top end portion of the conductive projection. When the conductive projection is reinforced by the resin material in a fillet form, a thermal
30 stress exerted on the conductive projection is not concentrated on a single point but dispersed, thus obtaining high junction

reliability. The resin material in a fillet form can be easily realized by means of a heating reflow apparatus under conditions for heating conventionally generally used.

[0014]

5 When the resin material contains an activator which assists in the junction between the conductive projection and the conductor portion when the resin material is in an uncured state, not only reinforcement of the junction portion but also cleaning or an improvement of the junction plane in wettability
10 can be achieved due to the action of the activator without applying a flux separately. As the activator used in the present invention, one having a property such that it loses its action after the curing reaction of the resin material is completed is used. Therefore, the activator does not lower
15 the insulation reliability without cleaning as conducted for a flux generally used.

[0015]

By using a resin material having photo-curing properties, when the resin material is selectively cured by a light, the
20 resin material can serve as a solder resist for covering and protecting the conductor portion other than the junction plane. By this method, there is no need to preliminarily form a solder resist. Further, before the heating step for the junction, the resin material is cured by a light, excluding the resin
25 material on the junction plane, the conductive projection can be prevented from suffering mispositioning or aggregation during the heating step.

[0016]

When the conductive projection has a core portion
30 encapsulated therein, a stress exerted on the junction portion of the conductive projection may be relaxed by using a material

having elasticity, e.g., a resin for the core portion.

[0017]

The junction method for conductive projection of the present invention includes the steps of: forming a conductor
5 portion on an insulating layer in such a way that the surface of the conductor portion is formed at the same level as that of the surface of the insulating layer; supplying a resin material in an uncured state onto at least a junction plane of the conductor portion to which a conductive projection is
10 joined; disposing the conductive projection on the junction plane which has the resin material supplied thereon; and heating the resin material and the conductive projection to join the conductive projection to the conductor portion while curing the resin material so that a root portion of the
15 conductive projection is surrounded by the resin material in a ring form.

[0018]

In this method, the steps on the surface to which the conductive projection is joined are removed and then the
20 reinforcing resin material is supplied to the resultant flat surface. Therefore, even if the amount of the resin material supplied is small, since the resin material is prevented from flowing into gaps on the surface, a larger amount of the resin material can be allowed to wet and rise the root portion of
25 the conductive projection, thus making it possible to form the resin material having a uniform height required for securing a satisfactory strength of the junction portion.

[0019]

As examples of methods for making the surface of the
30 conductor portion formed at the same level as that of the surface of the insulating layer, there can be mentioned a method in

which an insulating layer for planarization is supplied to the surface in a state such that the conductor portion is formed on the insulating layer, followed by polishing, and a method in which planarization is made by filling portions between the conductor portions with an insulating layer and the resultant material is formed on a transfer support, and bonded and transferred to the insulating layer to which the conductive projection is joined.

[0020]

10 The resin material is first supplied and then the conductive projection is disposed on and joined to the conductor portion, and hence the resin material is not deposited on the upper end portion side of the conductive projection, and therefore connection of the structure to another wiring board, such as a mother board, can be advantageously accomplished.

[0021]

 The resin material is supplied to at least the conductor portion which is the junction plane for the conductive projection, but the junction method may be carried out such that the resin material in an uncured state is supplied onto the entire surfaces of both of the conductor portion and the insulating layer, and cured by exposure, excluding the resin material on the junction plane, and then the conductive projection is disposed on the junction plane on which the resin material remains uncured, followed by heating the resin material and the conductive projection.

[0022]

 By this method, the portion of the resin material cured by exposure as such can serve as a solder resist for covering and protecting the conductor portion other than the junction

plane for the conductive projection. Further, the portion of the resin material cured by exposure controls the movement of the conductive projection during the heating step or the like, making it possible to prevent the conductive projection from suffering mispositioning or aggregation.

[0023]

By the present invention, the conductive projection is joined to the surface of the conductor portion which is formed at the same level as that of the surface of the insulating layer so that the root portion of the conductive projection is surrounded by the resin material in a ring form. Therefore, even when the amount of the resin material supplied is reduced for suppressing warpage, a fillet having a large height can be obtained to improve the junction portion in strength and reliability, as compared to that in a structure without planarization. Accordingly, high wiring density can be achieved by reducing the size of the conductive projection without increasing the number of layers of interconnection to cause the substrate to have a large thickness.

20

Brief Description of the Drawings

[0023]

The above and other objects, features and advantages of the present invention will become more apparent from the following description of the presently preferred exemplary embodiments of the invention taken in conjunction with the accompanying drawings, in which:

[0024]

FIGs. 1A and 1B are diagrammatic cross-sectional views illustrating steps in a junction method for conductive projection according to a first embodiment of the present

30

invention;

[0025]

FIGs. 2A and 2B are diagrammatic cross-sectional views illustrating steps subsequent to the step of FIG. 1B;

5 [0026]

FIGs. 3A and 3B are diagrammatic cross-sectional views illustrating steps subsequent to the step of FIG. 2B;

[0027]

FIGs. 4A and 4B are diagrammatic cross-sectional views illustrating steps subsequent to the step of FIG. 3B;

[0028]

FIG. 5 is an enlarged perspective view of a junction portion of a conductive projection in Example 1;

[0029]

15 FIG. 6 is an enlarged perspective view of a junction portion of a conductive projection in Comparative Example 1;

[0030]

FIGs. 7A and 7B are diagrammatic cross-sectional views illustrating steps in a junction method for conductive projection according to a second embodiment;

20 [0031]

FIGs. 8A and 8B are diagrammatic cross-sectional views illustrating steps subsequent to the step of FIG. 7B;

[0032]

25 FIGs. 9A and 9B are diagrammatic cross-sectional views illustrating steps in a junction method for conductive projection according to a third embodiment;

[0033]

FIGs. 10A to 10C are diagrammatic cross-sectional views illustrating steps for planarization of a surface of a substrate in a modified example;

30

[0034]

FIGs. 11A to 11C are diagrammatic cross-sectional views illustrating steps for planarization of a surface of a substrate in another modified example;

5 [0035]

FIG. 12 is an enlarged cross-sectional view of a junction portion of a conductive projection in Comparative Example 1;

[0036]

FIG. 13 is an enlarged cross-sectional view of a junction portion of a conductive projection in Comparative Example 2;

[0037]

FIG. 14 is an enlarged cross-sectional view of a junction portion of a conductive projection in Comparative Example 3; and

15 [0038]

FIG. 15 is a diagrammatic cross-sectional view of a conductive projection having one example of structure.

Description of the Preferred Embodiments

20 [0039]

Hereinbelow, preferred embodiments of the present invention will be described with reference to the drawings.

[0040]

First Embodiment

25 In the present embodiment, as one example of the junction structure and junction method of the present invention, a structure in which a conductive projection is joined to an interposer, on which conductor portions (wiring and land) are formed for rearrangement of electrode portions of a
30 semiconductor bare chip to be mounted is formed to a larger pitch, so that a root portion of the conductive projection

is reinforced by a resin, and a junction method for the structure will be described. FIGs. 1 to 4 illustrate process steps for the junction.

[0041]

5 Process Step of FIG. 1A

First, a substrate including an insulating layer 1 having formed on both surfaces thereof conductor portions 2a, 2b, 3 is prepared or provided. For example, the conductor portions 2a, 2b, 3 are formed in a desired pattern on the insulating
10 layer 1 by a subtractive method in which a flat metal foil is bonded onto the insulating layer 1 and then an unnecessary portion of the metal foil is etched, or an additive method in which the insulating layer 1 is subjected to pattern plating by electroless plating or electrolytic plating. The surface
15 of the conductor portion 2a is a junction plane to which the below-described conductive projection is joined.

[0042]

With respect to the materials for the insulating layer 1 and conductor portions 2a, 2b, 3, there is no particular
20 limitation, and they are appropriately selected depending on the properties required. As the insulating layer 1, for example, glass fiber impregnated with an epoxy resin, glass fiber impregnated with a polyimide resin, or paper impregnated with a phenolic resin may be used. Alternatively, a mixture
25 of an epoxy resin and a bismaleimide triazine resin, a liquid crystalline polymer, benzocyclobutene, or the like may be used. As a material for the conductor portions 2a, 2b, 3, generally, copper is often used, but other metals may be used as long as they satisfy a required electrical resistance value.

30 [0043]

A not shown step of forming a connection hole for

connecting the conductor portions 2a, 2b formed on one surface of the insulating layer 1 to the conductor portion 3 formed on another surface and forming a conductive material for filling the hole is conducted to make interlayer connection
5 between the conductor portions 2a, 2b and the conductor portion 3.

[0044]

Process Step of FIG. 1B

One surface of the substrate on which the conductor
10 portions 2a, 2b are formed is subjected to planarization. For example, first, a resin material in a paste state is applied to the one surface of the substrate so as to fill portions between the conductor portions 2a, 2b. Subsequently, the resin material is cured by heating or the like, and then polished
15 so that the surfaces of the conductor portions 2a, 2b are exposed. Thus, an insulating layer 4 is formed on the insulating layer 1 by filling portions between the conductor portions 2a, 2b and the surface of the insulating layer 4 is formed at the same level as those of the surfaces of the conductor portions
20 2a, 2b, thereby achieving planarization of the surface of the substrate to which a conductive projection is joined.

[0045]

Process Step of FIG. 2A

For example, a semiconductor bare chip 5 is mounted by
25 electrically connecting it to the conductor portion 3 formed on another surface of the insulating layer 1. In the connection between the semiconductor bare chip 5 and the conductor portion 3, for example, Au-Au junction, Au-Sn junction, Au-SnAg junction, or Sn-Ni junction is used. As examples of methods
30 for forming a metal layer for junction on the semiconductor bare chip 5, there can be mentioned a stud bump process and

a plating bump process. On the other hand, the conductor portion 3 may be subjected to surface treatment by, for example, a plating process to form a desired metal layer for junction on the conductor portion 3. When Ni is used as the metal layer for junction, Au or Pd may be plated in a small thickness (about several tens nm) on the surface of the Ni layer to prevent oxidation.

[0046]

For securing the mounting reliability of the semiconductor bare chip 5, a gap between the semiconductor bare chip 5 and the surface of the insulating layer 1 on which the semiconductor bare chip 5 is mounted may be filled with an underfill resin material. The filling with the resin material may be conducted either before or after the mounting of the semiconductor bare chip 5.

[0047]

Process Step of FIG. 2B

A resin material 6 is supplied to the entire surfaces of all of the insulating layer 4 and the conductor portions 2a, 2b after the planarization. As examples of methods for supplying the resin material 6, there can be mentioned a method in which a resin material diluted with a solvent to be in a liquid state is applied by a spraying process and then dried, a method in which a resin material in a paste state is supplied by a printing or spin coating process, and a method in which a resin material in a film form, which is not completely cured, for example, in a B-stage, is bonded to the surface, but the method is not particularly limited to these methods as long as a required amount of the resin material can be uniformly supplied. The required amount means an amount such that the below-described fillet has a height required for securing a

satisfactory junction strength.

[0048]

In the present embodiment, the resin material 6, for example, having ultraviolet curing properties and containing an activator is used. Specifically, the resin material 6 obtained by incorporating into a phenolic novolak containing at least an acryloyl group or a methacryloyl group a resin which serves as a curing agent for the phenolic novolak and a photopolymerization initiator is used. The phenolic hydroxyl group of the phenolic novolak functions as an activator, and removes contaminants, such as an oxide, from the surface of solder and a metal or prevents reoxidation due to its reducing action, thus improving the wettability of the solder or fused metal with respect to the surface of the conductor portion 2a which is the junction plane. The activator loses this action after the resin material 6 is cured.

[0049]

As the curing agent, an epoxy resin, an isocyanate resin, or the like is used. Specific examples include epoxy compounds and isocyanate compounds, each obtained by modifying a phenolic base compound, such as bisphenol, phenolic novolak, alkylphenolic novolak, biphenol, naphthol, or resorcinol, or an aliphatic, alicyclic, or unsaturated aliphatic base compound.

25 [0050]

Examples of photopolymerization initiators include benzophenones, such as benzophenone, benzoylbenzoic acid, 4-phenylbenzophenone, and hydroxybenzophenone; benzoin alkyl ethers, such as benzoin, benzoin methyl ether, benzoin dimethyl ether, benzoin ethyl ether, benzoin isopropyl ether, benzoin butyl ether, and benzoin isobutyl ether; acetophenones, such

as 4-phenoxydichloroacetophenone,
4-t-butyl-dichloroacetophenone,
4-t-butyl-trichloroacetophenone, and diethoxyacetophenone;
thioxanthenes, such as thioxanthone, 2-chlorothioxanthone,
5 2-methylthioxanthone, and 2,4-dimethylthioxanthone; and
alkylanthraquinones, such as ethylanthraquinone and
butylanthraquinone. These initiators may be used
individually or in the form of a mixture of two or more
initiators.

10 [0051]

Process Step of FIG. 3A.

On a portion of the resin material 6 over the conductor
portion 2a which is the junction plane for a conductive
projection 8, a resist mask 7 is formed by conventionally known
15 photolithography and etching. The other portions of the resin
material 6 are exposed, and irradiated with an ultraviolet
light in this state.

[0052]

Thus, a resin material 6a at a portion which is not covered
20 with the resist mask 7 is cured. The resin material 6a serves
as an insulating protective film (solder resist) for preventing
an occurrence of short-circuiting between the conductor
portions 2b, between the conductor portions 2a, 2b, or between
the conductor portion 2b and the conductive projection 8.
25 Therefore, there is no need to form a solder resist separately,
enabling the process step to be simplified.

[0053]

Process Step of FIG. 3B

After removing the resist mask 7, a spherical conductive
30 projection 8 is disposed on the surface of the conductor portion
2a on which the resin material 6 remains uncured. With respect

to the material for the conductive projection 8, there is no particular limitation, and a material having a conventionally known alloy composition, such as Sn-Pb, Sn-Ag, Sn-Ag-Cu, Sn-Zn, or Sn-Zn-Bi, is used.

5 [0054]

Alternatively, a conductive projection 48 shown in FIG. 15 having encapsulated therein a core portion 48a comprised of, e.g., a resin material may be used. The surface of the core portion 48a is coated with a conductive surface layer portion which includes a metal layer 48b and a solder plated layer 48c. By virtue of having the core portion 48a encapsulated, the whole of the conductive projection receives an external stress, thus relaxing a stress at the junction portion. In addition, the gap between an interposer and a mother board which are connected together through the conductive projection 48 is kept uniform, realizing high junction reliability. The core portion 48a may be comprised of any material as long as it has stress relaxation properties and consistent diameter, and the material is not limited to a resin but may be a rubber or a metal.

20

[0055]

Process Step of FIG. 4A

This is a process step for placing the interposer having mounted thereon the conductive projection 8 in a reflow process furnace to heat it. The conductive projection 8 disposed on the conductor portion 2a is brought by gravity into contact with the surface of the conductor portion 2a, and fused by further heating, and the fused conductive projection 8 wets and spreads the surface of the conductor portion 2a so as to push away the uncured resin material 6, thus achieving metal junction between the conductive projection 8 and the conductor

30

portion 2a.

[0056]

5 The resin material 6 at a portion on which the conductive projection 8 is disposed is uncured upon reflow and hence has a metal activating action due to the included activator described above, and therefore the wettability between the conductive projection 8 and the conductor portion 2a can be improved without applying a flux separately, thus enabling a high level of junction strength.

10 [0057]

Further, the heating in this instance allows the uncured resin material 6 to wet the root portion (portion on the side of the junction portion to the conductor portion 2a) of the conductive projection 8 and spread in a ring form to form a fillet 6b surrounding the root portion, and cured by further heating.

[0058]

20 The insulating layer 4 fills the portions between the conductor portions 2a, 2b and the surface to which the conductive projection 8 is joined is flat by planarization, and therefore the uncured resin material 6 is prevented from flowing into the portions between the conductor portions 2a, 2b when forming the fillet 6b, thus making it possible to increase the amount of the resin material which wets and spreads the root portion of the conductive projection 8.

[0059]

30 Accordingly, a fillet having a large height can be obtained, as compared to a conventional fillet formed when there is a step between the junction plane and the surface of the insulating layer and no planarization is conducted (when the amount of the reinforcing resin material supplied is the

same), and thus the junction strength of the conductive projection 8 can be improved.

[0060]

The resin material 6 having photo-curing properties and
5 containing an activator cannot contain filler in a large amount
and is likely to suffer relatively large shrinkage on curing
due to its properties. Therefore, for suppressing warpage
of the interposer or semiconductor bare chip 5, it is
advantageous that the amount of the resin material 6 supplied
10 is as small as possible. In the present embodiment, as
mentioned above, the surface to which the resin material 6
is supplied is flat by planarization, and hence the resin
material 6 supplied even in a small amount can realize a fillet
height required for securing a satisfactory strength. The
15 fillet height required for securing a satisfactory strength
varies depending on the type of the resin material or the
material for or size of the conductive projection 8, but a
satisfactory fillet height may be, for example, 10 percent
of the height of the conductive projection 8 or more.

20 [0061]

In the resin material (e.g., epoxy resin) 4 used for
planarization, filler (e.g., powder of silicate) may be added
to optimize physical properties, such as a coefficient of
thermal expansion, of the resin material, making it possible
25 to lower the shrinkage on curing and suppress warpage of the
interposer or semiconductor bare chip 5.

[0062]

In addition, when the resin material 6 is supplied onto
a flat surface, the thickness of the resin material 6 supplied
30 on the surface can be uniform, thus making it possible to form
the fillet 6b having a consistent height. Therefore, a

difference in the junction strength between the conductive projections 8 disposed at different positions is suppressed, preventing a stress from locally concentrating on the conductive projection 8 having a small junction strength.

5 [0063]

Further, when the resin material 6a being present between the conductive projections 8 and protecting the conductor portions 2b is cured by exposure before fusing the conductive projections 8 by heating, the conductive projections 8 can
10 be prevented from undergoing aggregation during the fusing by heating. In other words, the resin material 6a cured by exposure has also a function of positioning the individual conductive projections 8 at the corresponding conductor portions 2a and joining them together.

15 [0064]

Finally, a dicing treatment is performed, thus obtaining a semiconductor part in which, as shown in FIG. 4B, the conductive projection 8 which serves as an external connection terminal is joined to the surface of the conductor portion
20 2a which is formed at the same level as that of the surface of the insulating layer 4 so that the root portion of the conductive projection 8 is surrounded by the fillet 6b comprised of a resin material. By employing this junction structure, there can be obtained a structure such that the
25 amount of the reinforcing resin material 6 can be reduced for suppressing warpage while maintaining the fillet height required for securing a desired strength. This junction structure is effective especially for junction of the conductive projection 8 which tends to become smaller for
30 meeting the demands of reduction in thickness and increase in pins.

[0065]

Second Embodiment

Next, the second embodiment of the present invention will be described. In the first and second embodiments, like constituent parts or portions are indicated by like reference numerals, and the overlapping detailed description is omitted.

[0066]

In the first embodiment, as the resin material 6 for reinforcing the junction portion, an ultraviolet-curing resin material is mentioned as an example, but, when forming the fillet 6b around the root portion of the conductive projection 8, the resin material does not necessarily have ultraviolet curing properties.

[0067]

In this case, the resin material 6 does not serve as a solder resist for protecting the conductor portion 2b and hence, as shown in FIG. 7A, there is a need to form a solder resist 9 for covering the conductor portion 2b on the surface of the insulating layer 4 which has preliminarily been subjected to planarization.

[0068]

Then, as shown in FIG. 7B, the resin material 6 in a paste state is supplied by a printing process only to the conductor portion 2a and its periphery portion.

[0069]

Then, without the step for ultraviolet light irradiation as conducted in the first embodiment, as shown in FIG. 8A, the conductive projection 8 is disposed on the resin material 6 and conductor portion 2a, and subjected to reflow heating in the same manner as in the first embodiment to join together the conductive projection 8 and the conductor portion 2a and

allow the resin material 6 to wet and rise the root portion of the conductive projection 8, thus forming a fillet 6b surrounding the root portion, followed by curing by further heating (FIG. 8B).

5 [0070]

In the present embodiment, the insulating layer 4 fills the portions between the conductor portions 2a, 2b and the surface to which the conductive projection 8 is joined is flat by planarization, and therefore the uncured resin material
10 6 is prevented from flowing into the portions between the conductor portions 2a, 2b when forming the fillet 6b, thus making it possible to increase the amount of the resin material which wets and spreads the root portion of the conductive projection 8. Substantially the same effect as that obtained
15 in the first embodiment can be obtained except that the resin material 6 does not serve as a solder resist.

[0071]

Next, the results of measurement of a shear strength in Example 1 employing the junction structure and junction
20 method similar to those in the second embodiment are shown while comparing with the results in Comparative Examples 1 to 3 corresponding to prior art techniques.

[0072]

Structure of Example 1

25 FIG. 5 is a perspective view of an essential portion of a substrate for evaluation in Example 1. A printed wiring board including a base material 14 having a 30 mm × 30 mm size, having 12 points of copper lands (conductor portions) 12 each having a diameter of 300 μm, and having 12 points of copper
30 lands (conductor portions) 12 each having a diameter of 200 μm was prepared, and this printed wiring board was used as

a substrate for evaluation. As the base material, glass fiber impregnated with an epoxy resin (grade FR-4) was polished. The base material has a thickness of 0.4 mm, and each conductor portion 12 has a thickness of 18 μm .

5 [0073]

An insulating layer 14 comprised of an epoxy resin was applied to the evaluation substrate so that the thickness of the layer became 20 μm , and cured to cover the conductor portions 12 and fill portions between the conductor portions 12.

10 Subsequently, the cured insulating layer 14 was abraded so that the surfaces of the conductor portions 12 were exposed, thus achieving a planarization treatment for the evaluation substrate.

[0074]

15 Subsequently, an epoxy resin material having thermosetting properties and containing a metal activator was supplied by a printing process using a screen mask having an opening diameter of 300 μm and a thickness of 60 μm only onto the conductor portions 12 of the evaluation substrate which
20 had been subjected to planarization treatment, and solder balls (Sn63Pb37 composition) 18 each having a diameter of 300 μm were mounted as conductive projections on the resin material.

[0075]

Then, reflow heating at a peak temperature of 220°C was
25 conducted to join the solder ball 18 to the conductor portion 12. Further, heating at 150°C was conducted for 1 hour to completely cure the resin material containing a metal activator.

[0076]

30 Thus, a structure shown in FIG. 5 was obtained in which the root portion of the solder ball 18 was surrounded by the

resin material 16 in a fillet form.

[0077]

Subsequently, a shear strength of the solder ball 18 was measured. The shear strength at the conductor portions 12 having a diameter of 300 μm was 0.58×9.80665 (N) (average value of 12 points), and the shear strength at the conductor portions 12 having a diameter of 200 μm was 0.49×9.80665 (N) (average value of 12 points).

[0078]

10 Structure of Comparative Example 1

Substantially the same procedure as in Example 1 was repeated except that no planarization treatment for the evaluation substrate was conducted to form solder balls 18. The form of the resin material reinforcing the solder ball 18 is shown in FIG. 6 and FIG. 12. The root portion of the solder ball 18 was surrounded by the resin material 46 like in Example 1, but the surface to which the reinforcing resin material was supplied was not subjected to planarization treatment, and hence the resin material supplied disadvantageously flowed into the gaps between the conductor portions 12. Therefore, although the amount of the resin material printed was the same, the height of the resin material 46 was only about 1/2 to 1/3 of that in Example 1.

[0079]

Subsequently, a shear strength of the solder ball 18 in Comparative Example 1 was measured. The shear strength at the conductor portions 12 having a diameter of 300 μm was 0.45×9.80665 (N) (average value of 12 points), and the shear strength at the conductor portions 12 having a diameter of 200 μm was 0.38×9.80665 (N) (average value of 12 points).

[0080]

Structure of Comparative Example 2

Substantially the same procedure as in Example 1 was repeated except that, instead of the resin material containing a metal activator, a general flux (BF-31; manufactured and sold by TAMURA KAKEN Corporation) was used for junction to form solder balls 18. The junction structure obtained is shown in FIG. 13. The reinforcement structure by the resin material seen in Example 1 and Comparative Example 1 was not observed around the root portion of the solder ball 18.

10 [0081]

Subsequently, a shear strength of the solder ball 18 in Comparative Example 2 was measured. The shear strength at the conductor portions 12 having a diameter of 300 μm was 0.43×9.80665 (N) (average value of 12 points), and the shear strength at the conductor portions 12 having a diameter of 200 μm was 0.26×9.80665 (N) (average value of 12 points).

[0082]

Structure of Comparative Example 3

Substantially the same procedure as in Example 1 was repeated except that, instead of the resin material containing a metal activator, a general flux (BF-31; manufactured and sold by TAMURA KAKEN Corporation) was used, and that no planarization treatment for the evaluation substrate was conducted to form solder balls 18. The junction structure obtained is shown in FIG. 14. The reinforcement structure by the resin material seen in Example 1 and Comparative Example 1 was not observed around the root portion of the solder ball 18.

[0083]

Subsequently, a shear strength of the solder ball 18 in Comparative Example 3 was measured. The shear strength

at the conductor portions 12 having a diameter of 300 μm was 0.43×9.80665 (N) (average value of 12 points), and the shear strength at the conductor portions 12 having a diameter of 200 μm was 0.25×9.80665 (N) (average value of 12 points).

5 [0084]

The results of measurement of the shear strength are shown in Table 1.

[0085]

Table 1

10 Shear strength of conductive projection

Land diameter	300 μm	200 μm
Example 1	0.58	0.49
Comparative Example 1	0.45	0.38
Comparative Example 2	0.43	0.26
Comparative Example 3	0.43	0.25

{ $\times 9.80665$ (N) }

[0086]

As apparent from Table 1, a structure in which the root portion of the solder ball 18 is surrounded and reinforced by the resin material on the evaluation substrate which has been subjected to planarization, namely, the junction structure in Example 1 exhibits the highest shear strength with respect to each of the conductor portions having a diameter of 300 μm and the conductor portions having a diameter of 200 μm . Particularly, the shear strength at the conductor portions having a diameter of 200 μm in Example 1 is higher than the shear strength of the structure in Comparative Example 3 at the conductor portions having a diameter of 300 μm conventionally generally used, which indicates that the junction structure in Example 1 using the junction structure of the present invention can be advantageously put into

practical use even when the diameter of the conductor portions is 200 μm .

[0087]

5 If some rosin flux generally used remains due to a lack of cleaning, a structure such that the remaining flux covers the periphery of a conductive projection is possibly obtained, but this structure is too brittle to serve as a reinforcing material for the junction portion.

[0088]

10 Third Embodiment

The junction structure and junction method for conductive projection of the present invention can be applied not only to an interposer but also to a so-called wafer level chip size package (CSP) which performs rewiring or formation of conductive projection collectively in the form of a wafer.

[0089]

Specifically, in FIG. 9A, a plurality of micro-electrode portions 30a for semiconductor integrated circuit formed on the surface of a semiconductor wafer 30 comprised of silicon or the like are rearranged through conductor portions 31 formed by opening an insulating protective film 32 to conductor portions 34 which are connected to the conductor portions 31 and which have a pitch further enlarged.

[0090]

25 Portions between the conductor portions 34 are filled with an insulating layer 33 by a method similar to the method described above with reference to FIG. 1B, so that the surface of the conductor portion 34 is formed at the same level as that of the surface of the insulating layer 33.

30 [0091]

Then, on the flat surface by planarization, a structure

shown in FIG. 9B, in which a conductive projection 8 is joined to the conductor portion 34 so that the root portion of the conductive projection 8 is surrounded and reinforced by a fillet 6b, is obtained through steps similar to the above steps
5 shown in FIGs. 2B to 4A.

[0092]

In the present embodiment, the same effect as that obtained in the first embodiment can be obtained, but, in the wafer level CSP which is largely affected by a stress caused
10 due to a difference in the coefficient of thermal expansion between the wafer 30 comprised of silicon or the like and the mother board comprised of a resin material or the like, the conductive projection 8 is required to have a higher junction strength, and, for the reason that reduction of the size of
15 the conductive projection 8 for increasing the wiring density can be conducted in a smaller cost than the cost for further increasing the number of the layers of interconnection, the above-described structure using planarization and reinforcement by a resin material in combination is especially
20 effective.

[0093]

Hereinabove, the preferred embodiments of the present invention are described, but the present invention is not limited to these and can be changed or modified based on the
25 technical concept of the present invention.

[0094]

In the first embodiment, the planarization treatment is performed in such a state that the conductor portions 2a, 2b are preliminarily formed on the insulating layer 1, but,
30 for example, when, as shown in FIG. 10A, the conductor portions 2a, 2b are formed on the surface of a support 40 comprised

of a metal through a release layer (not shown) and subjected to planarization treatment using an insulating layer 41, and the resultant material is bonded to the insulating layer 1 (FIG. 10B) and then the support 40 is peeled off, the formation
5 of the conductor portions 2a, 2b on the insulating layer 1 and the planarization treatment for the insulating layer 1 can be achieved simultaneously (FIG. 10C).

[0095]

Alternatively, as shown in FIG. 11A, the conductor
10 portions 2a, 2b are formed on the surface of the support 40 through a release layer (not shown), and the resultant material is bonded to the insulating layer 1 so that the conductor portions 2a, 2b are embedded in the insulating layer 1 (FIG. 11B) and then the support 40 is peeled off (FIG. 11C).

15 [0096]

Finally, the embodiments and examples described above are only examples of the present invention. It should be noted that the present invention is not restricted only to such
embodiments and examples, and various modifications,
20 combinations and sub-combinations in accordance with its design or the like may be made without departing from the scope of the present invention.